

AUTOMOTIVE CURRENT TRANSDUCER OPEN LOOP TECHNOLOGY HC5FW 500-S









Introduction

The HC5FW family is for the electronic measurement of DC, AC or pulsed currents in high power and low voltage automotive applications with galvanic separation between the primary circuit (high power) and the secondary circuit (electronic circuit).

The HC5FW family gives you the choice of having different current measuring ranges in the same housing.

Features

- · Open Loop transducer using the Hall effect
- Low voltage application
- Unipolar +5 V DC power supply
- Primary current measuring range up to ±500 A
- Maximum RMS primary current limited by the busbar, the magnetic core or the ASIC temperature T < +150 °C
- Operating temperature range: -40 °C < T < +125 °C
- Output voltage: full ratiometric (sensitivity and offset)
- · High speed transducer.

Advantages

- Good accuracy
- Good linearity
- Low thermal offset drift
- Low thermal sensitivity drift.

Automotive applications

- Electrical Power Steering
- Starter Generators
- Converters.

Principle of HC5FW Family

The open loop transducers use a Hall effect integrated circuit. The magnetic flux density *B*, contributing to the rise of the Hall voltage, is generated by the primary current $I_{\scriptscriptstyle D}$ to be measured. The current to be measured I_p is supplied by a current source i.e. battery or generator (Figure 1).

Within the linear region of the hysteresis cycle, B is proportional to:

$$B\left(I_{\mathsf{P}}\right) = a \times I_{\mathsf{P}}$$

The Hall voltage is thus expressed by:

$$U_{\mathsf{Hall}} = (c_{\mathsf{Hall}} / d) \times I_{\mathsf{Hall}} \times a \times I_{\mathsf{P}}$$

Except for I_{p} , all terms of this equation are constant. Therefore:

> $U_{\rm Hall} = b \times I_{\rm P}$ constant h constant Hall coefficient

thickness of the Hall plate current across Hall plate

The measurement signal $U_{\rm Hall}$ is amplified to supply the user output voltage or current.

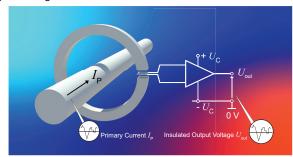
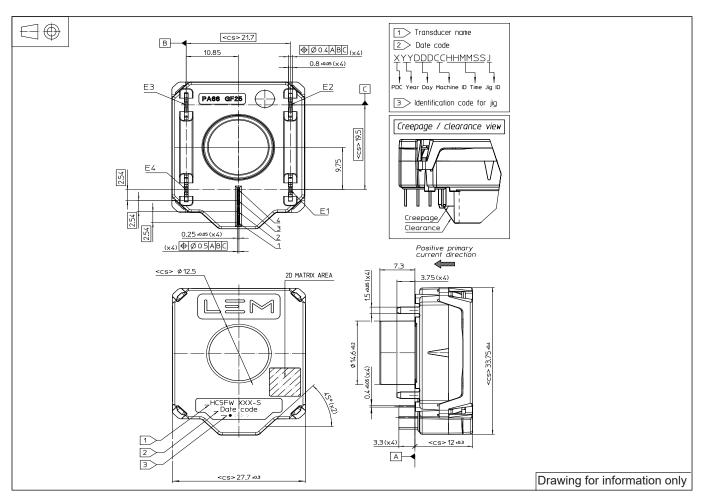


Fig. 1: Principle of the open loop transducer



Dimensions HC5FW 500-S series (in mm)



Mechanical characteristics

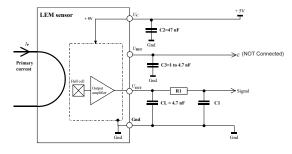
Plastic case
 Magnetic core
 Plastic cover
 PA 66 GF 25
 FeSi alloy
 PA 6T/66 GF 30

Mass 27.5 gElectrical terminal coating Tin plated

Mounting recommendation

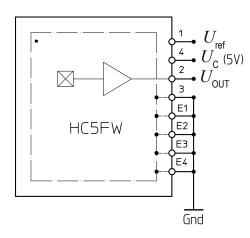
Connector type None
 Assembly torque max None
 Soldering profile See page 7

Electronic schematic



Remarks

- $I_{\rm P} = \left(\frac{5}{U_{\rm C}} \times U_{\rm out} U_{\rm O}\right) \times \frac{1}{S}$ with S in (V/A)
- $U_{\rm out}$ > $U_{\rm O}$ when $I_{\rm P}$ flows in the positive direction (see arrow on drawing).
- R1, C1: low pass filter (optional).





Absolute ratings (not operating)

HC5FW 500-S

Parameter	Symbol	Unit	Specification			O continue
			Min	Typical	Max	Conditions
Maximum supply voltage	$U_{\rm C\; max}$	V			8	not operating
					6.5	Exceeding this voltage may temporary reconfigure the circuit until the next power-on
Maximum primary current peak	$\hat{I}_{P\;max}$	А			3)	
Ambient storage temperature	T_{Ast}	°C	-40		125	
Electrostatic discharge voltage	$U_{\mathrm{ESD\; HBM}}$	kV			2	JESD22-A114-B class 2
Maximum admissible vibration (random)	γ _{max}	m∙s ⁻²		90		10 to 1000 Hz
RMS voltage for AC insulation test, 50 Hz, 1 min	$U_{\rm d}$	kV			2.5	50 Hz, 1 min, IEC 60664 part1
Insulation resistance	R _{INS}	МΩ	500			
Creepage distance	d_{Cp}	mm	7.1			
Clearance	d_{CI}	mm	5.5			
Comparative traking index	CTI	V	550 on case / 600 on cover		cover	
Maximum reverse current	I _{rev max}	mA	-80		80	

Operating characteristics in nominal range ($I_{\rm P\,N}\!)$

			Specification			
Parameter	Symbol	Unit	Min	Typical	Max	Conditions
		Elect	rical Data			
Primary current, measuring range	I_{PM}	Α	-500		500	
Primary nominal DC or RMS current	I_{PN}	Α	-500		500	
Supply voltage 1)	U_{C}	V	4.75	5.00	5.25	
Ambient operating temperature	T_{A}	°C	-40		125	
Output voltage (Analog)	U_{out}	V	$U_{\text{out}} = (U_{\text{c}}/5) \times (U_{\text{o}} + S \times I_{\text{p}})$			@ U _C
Sensitivity	S	mV/A		4		@ $U_{\rm C}$ = 5 V
Offset voltage	U_{o}	٧		2.5		@ $T_{\rm A}$ = 25 °C, @ $U_{\rm C}$ = 5 V, Hysteresis included
Current consumption	I_{C}	mA		19	25	@ $U_{\rm C}$ = 5 V, -40 °C < $T_{\rm A}$ < 125 °C
Load resistance	R_{L}	ΚΩ	10			
Load capacitance	C_{L}	nF		4.7	6.8	
Output internal resistance	$R_{\rm out}$	Ω			10	DC to 1 KHz
		Perform	ance Data 1)			
Ratiometricity error	$\varepsilon_{_{\Gamma}}$	%		0.5		
Sensitivity error	$\varepsilon_{_{ m S}}$	%		± 0.6		@ T _A = 25 °C
Electrical offset voltage	U_{OE}	mV		± 2.5		@ $T_{\rm A}$ = 25 °C, @ $U_{\rm C}$ = 5 V
Magnetic offset voltage	U_{OM}	mV		± 2		@ $T_{\rm A}$ = 25 °C, @ $U_{\rm C}$ = 5 V, after ± $I_{\rm P}$
Total error @ 0 A	$arepsilon_{ ext{tot}}$	mV	-13		13	@ $T_{\rm A}$ = 25 °C, @ $U_{\rm C}$ = 5 V, Hysteresis included
Average temperature coefficient of U_{OE}	TCU_{OEAV}	mV/°C	-0.08		0.08	@ -40 °C < T < 125 °C
Average temperature coefficient of S	TCS_{AV}	%/°C	-0.03		0.03	@ -40 °C < T < 125 °C
Linearity error	ε_{L}	% I _P	-1		1	Of full range
Delay time to 90 % to the final output value for I_{PN}						
step	t _{D 90}	μs		2	6	$di/dt = 100 \text{ A/}\mu\text{s}$
Frequency bandwidth 2)	BW	kHz	40			@ -3 dB
Phase shift	$\Delta \varphi$	0	-4		0	@ DC to 1 kHz
Minimum output voltage	$U_{ m outmin}$	V			0.2	@ U _C = 5 V
Maximum output voltage	U _{out max}	V	4.8			@ U _C = 5 V
Peak-to-peak noise voltage	U _{no pp}	mV			12	DC to 1 MHz

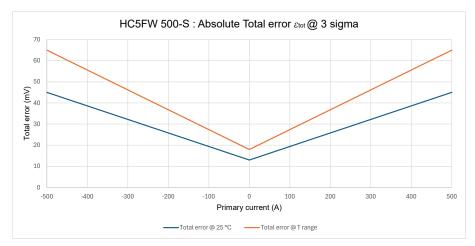
The output voltage U_{out} is fully ratiometric. The offset and sensitivity are dependent on the supply voltage U_{C} relative to the following formula: $I_{\text{P}} = \left(\frac{5}{U_{\text{C}}} \times U_{\text{out}} - U_{\text{O}}\right) \times \frac{1}{S} \text{ with } S \text{ in (V/A)}$ Notes:

$$I_{\mathsf{P}} = \left(\frac{5}{U_{\mathsf{C}}} \times U_{\mathsf{out}} - U_{\mathsf{O}}\right) \times \frac{1}{S} \text{ with } S \text{ in (V/A)}$$

- ²⁾ Small signal only to avoid excessive heating of the busbar, the magnetic core and the ASIC
- 3) Busbar temperature must be below 150 °C.

Page 3/7

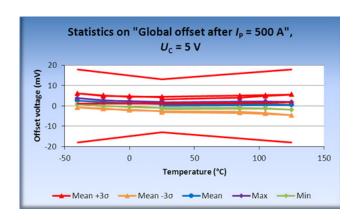


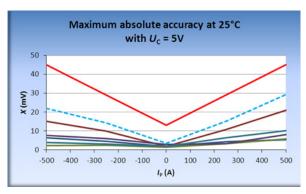


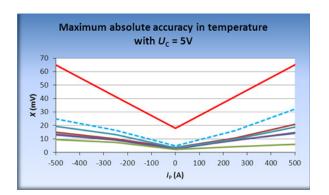
I _P (A)	Total error @ 25 °C (mV)	Total error @ T range (mV)
-500	± 45	± 65
0	± 13	± 18
500	± 45	± 65

Accuracy error specified at ± 3 Sigma.

Curves extracted from PV tests report.





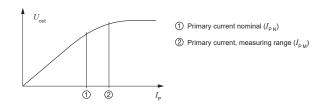


Curves in red line represent the tolerance Curves in dotted blue line represent average + 3 sigma.



PERFORMANCES PARAMETERS DEFINITIONS

Primary current definition:



Definition of typical, minimum and maximum values:

Minimum and maximum values for specified limiting and safety conditions have to be understood as such as values shown in "typical" graphs. On the other hand, measured values are part of a statistical distribution that can be specified by an interval with upper and lower limits and a probability for measured values to lie within this interval. Unless otherwise stated (e.g. "100 % tested"), the LEM definition for such intervals designated with "min" and "max" is that the probability for values of samples to lie in this interval is 99.73 %. For a normal (Gaussian) distribution, this corresponds to an interval between -3 sigma and +3 sigma. If "typical" values are not obviously mean or average values, those values are defined to delimit intervals with a probability of 68.27 %, corresponding to an interval between -sigma and +sigma for a normal distribution. Typical, minimum and maximum values are determined during the initial characterization of a product.

Output noise voltage:

The output voltage noise is the result of the noise floor of the Hall elements and the linear amplifier.

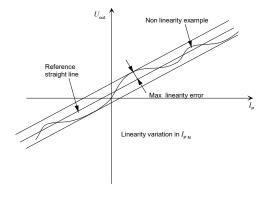
Magnetic offset:

The magnetic offset is the consequence of an any current on the primary side. It's defined after a stated excursion of primary current.

Linearity:

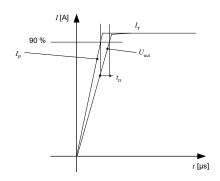
The maximum positive or negative discrepancy with a reference straight line U = f(I)

straight line $U_{\rm out}$ = $f(I_{\rm P})$. Unit: linearity (%) expressed with full scale of $I_{\rm P\,N}$.



Delay time $t_{D 90}$:

The time between the primary current signal $(I_{\rm P\ N})$ and the output signal reach at 90 % of its final value.



Sensitivity:

The transducer's sensitivity S is the slope of the straight line $U_{\text{out}} = f(I_{\text{p}})$, it must establish the relation:

$$U_{\text{out}}\left(I_{\text{P}}\right) = U_{\text{C}}/5\left(S \times I_{\text{P}} + U_{\text{O}}\right)$$

Offset with temperature:

The error of the offset in the operating temperature is the variation of the offset in the temperature considered with the initial offset at 25 $^{\circ}$ C.

The offset variation $I_{\rm O\,\it T}$ is a maximum variation the offset in the temperature range:

$$I_{\text{O}\,\text{T}} = I_{\text{O}\,\text{E}}\,\max\,-\,I_{\text{O}\,\text{E}}\,\min$$

The offset drift TCI_{OEAV} is the $I_{\text{O}T}$ value divided by the temperature range.

Sensitivity with temperature:

The error of the sensitivity in the operating temperature is the relative variation of sensitivity with the temperature considered with the initial offset at $25\,^{\circ}\text{C}$.

The average temperature coefficient of sensitivity TCS_{AV} , S_{T} is the maximum temperature variation of S (in ppm or %) of the sensitivity in the temperature range:

 S_{τ} = (Sensitivity max – Sensitivity min) / Sensitivity at 25 °C. The average temperature coefficient of sensitivity TCS_{av} is the

 S_{τ} value divided by the temperature range.

Deeper and detailed info available is in our LEM technical sales offices (www.lem.com).

Offset voltage @ I_p = 0 A:

The offset voltage is the output voltage when the primary current is zero. The ideal value of $U_{\rm O}$ is $U_{\rm C}/2$. So, the difference of $U_{\rm O}$ – $U_{\rm C}/2$ is called the total offset voltage error. This offset error can be attributed to the electrical offset (due to the resolution of the ASIC quiescent voltage trimming), the magnetic offset, the thermal drift and the thermal hysteresis. Deeper and detailed info available is in our LEM technical sales offices (www.lem. com).



Name	Standard					
THERMAL FATISUE						
Ageing 85 °C / 85 % <i>HR</i> / 1000 h Thermal cycle test -40 °C / 125 °C / 1000 h Thermal shocks -40 °C / 125 °C / 1000 h High temperature storage at 125 °C / 1000 h Low temperature storage at -50 °C / 1000 h MECHANICAL FATI Shocks test (50 m·s² x 10 x 3 axis) Vibration test (random 10 - 2000 Hz / 9.723 g)	IEC 60068-2-78 (2001) IEC 60068-2-14 test Nb (01.2009) IEC 60068-2-14 test Na (01.2009) IEC 60068-2-2 (07.2007) IEC 60068-2-1 (03.2007) GUE IEC 60068-2-27 test Ea (2008)					
ELECTRICAL TESTS						
Phase delay Output noise di/dt (100 A/µs) dv/dt (2 kV/µs to 2 kV) Withstand voltage (2500 V RMS -50 Hz / 1 min) Insulation resistance (500 V DC / 1 min)	98.20.00.575.0 98.20.00.545.0 98.20.00.545.0 ISO 16750-2 (2012)					
EMC TESTS						
Radiated Emissions: Absorber Lined Shielded Enclosure (ALSE) Radiated Immunity: Bulk Current Injection (BCI) Radiated Immunity: Anechoic chamber Resistance to Electrostatic Discharge Voltage	IEC CISPR25 ISO 11452-1 & -4 ISO 11452-1 & -2 ISO 10605 (2001)					

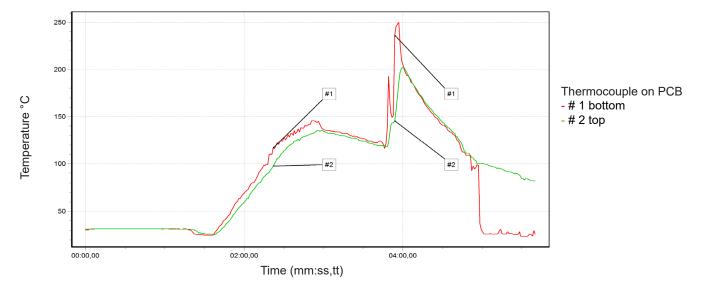


Soldering recommendations:

- 1 Iron Soldering plated-through holes device
- Mass pin (E1 to E4 see on drawing page 2): 200 W / 370 °C Iron temperature / 7 mm flat W200 Weller
- ASIC terminals (1,2,3,4 see on drawing page 2): 80 W / 410 °C Iron temperaure / 0.8 mm diameter STTC125 Metcal
- 2 Wave soldering plated-through holes device

LEM recommends to use the following equipment/parameters for the soldering of the HC5FW family in order to be compliant with the IPC A-610 (more than 75 % land coverage):

- Machine VITRONICS SOLTEC 6622 in combi wave mode
- Flux SLS 65
- Sn96 lead free solder (SAC 305)
- Temperature profile as below
- PCB 2143-00 thickness: 1.6 mm mass pin E1 to E4: hole Ø 2 Asic pin: hole Ø 1.



- 3 SMD soldering by pin in paste STH (SMD through hole)
- Must be validated by user
- ASIC MSL 1 level.